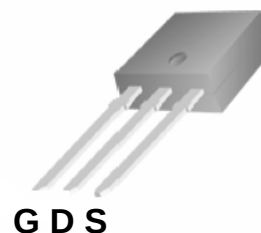




V_{DSS}	650	V
I_D	6	A
$P_D(T_C=25^{\circ}\text{C})$	85	W
$R_{DS(ON)Typ}$	1.4	Ω

PIN Connection TO-251



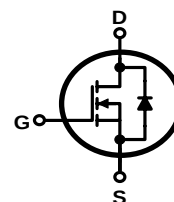
Features:

- Fast Switching
- Low ON Resistance($R_{ds(on)} \leq 1.7\Omega$)
- Low Gate Charge (Typical Data:19nC)
- Low Reverse transfer capacitances(Typical:7pF)
- 100% Single Pulse avalanche energy Test

Applications:

Power switch circuit of adaptor and charger.

Schematic diagram



Marking Diagram



Y = Year
A = Assembly Location
WW = Work Week
FIR6N65BP = Specific Device Code

Absolute (Tc= 25°C unless otherwise specified):

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	650	V
I_D	Continuous Drain Current	6	A
	Continuous Drain Current $T_C = 100^{\circ}\text{C}$	3.5	A
I_{DM}^{a1}	Pulsed Drain Current	20	A
V_{GS}	Gate-to-Source Voltage	± 30	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	250	mJ
E_{AR}^{a1}	Avalanche Energy ,Repetitive	26	mJ
I_{AR}^{a1}	Avalanche Current	2.3	A
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	85	W
	Derating Factor above 25°C	0.68	W/°C
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	°C
T_L	Maximum Temperature for Soldering	300	°C

**Electrical Characteristics** (Tc= 25°C unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	650	--	--	V
Δ BV _{DSS} / Δ T _J	Bvdss Temperature Coefficient	ID=250uA, Reference 25°C	--	0.71	--	V/°C
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 650V, V _{GS} = 0V, T _a = 25°C	--	--	1	μA
		V _{DS} =520V, V _{GS} = 0V, T _a = 125°C	--	--	250	
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} =+30V	--	--	100	nA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} =-30V	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =3A	--	1.4	1.7	Ω
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Pulse width tp ≤ 380μs, δ ≤ 2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g _{fs}	Forward Transconductance	V _{DS} =30V, I _D =6A	--	10	--	S
C _{iss}	Input Capacitance	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz	--	706	--	pF
C _{oss}	Output Capacitance		--	71	--	
C _{rss}	Reverse Transfer Capacitance		--	7	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	I _D =6A V _{DD} =325V V _{GS} = 10V R _G =12Ω	--	9	--	ns
t _r	Rise Time		--	15.5	--	
t _{d(OFF)}	Turn-Off Delay Time		--	36	--	
t _f	Fall Time		--	21	--	
Q _g	Total Gate Charge	I _D =6A V _{DD} =325V V _{GS} = 10V	--	19	--	nC
Q _{gs}	Gate to Source Charge		--	3.5	--	
Q _{gd}	Gate to Drain ("Miller") Charge		--	8	--	



Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	6	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	20	A
V_{SD}	Diode Forward Voltage	$I_S=6A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=6A, T_J = 25^\circ C$	--	192	--	ns
Q_{rr}	Reverse Recovery Charge	$dI_F/dt=100A/us, V_{GS}=0V$	--	844	--	nC
Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$						

Symbol	Parameter	Typ.	Units
$R_{\theta JC}$	Junction-to-Case	1.47	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	110	$^\circ C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=10.0mH, I_D=7.1A, \text{Start } T_J=25^\circ C$

^{a3}: $I_{SD}=6A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}, \text{Start } T_J=25^\circ C$

Characteristics Curve:

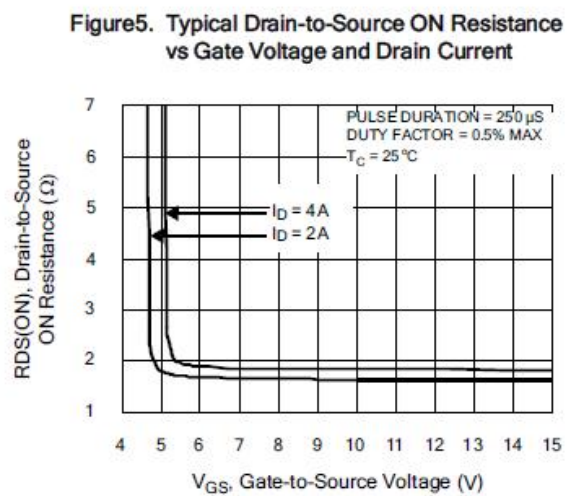
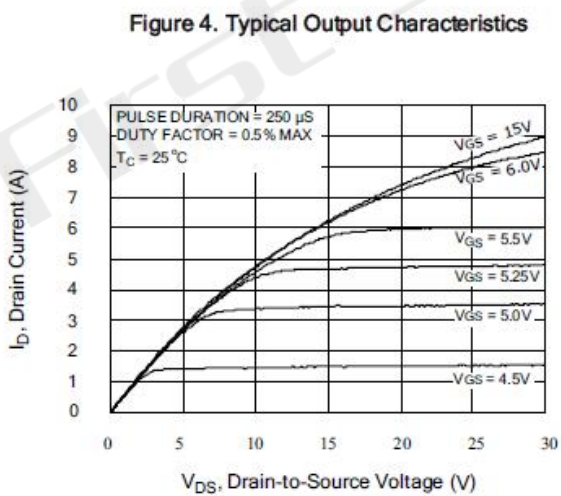
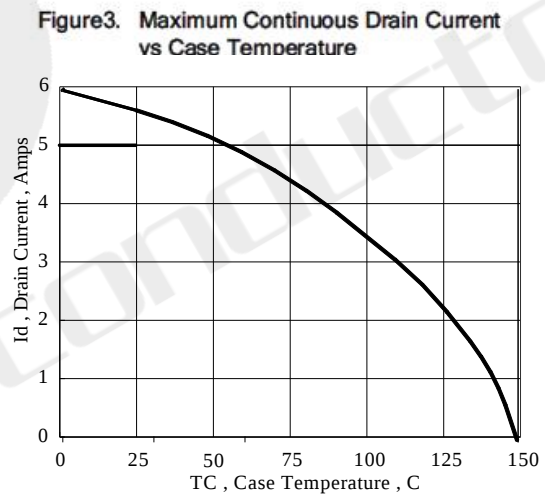
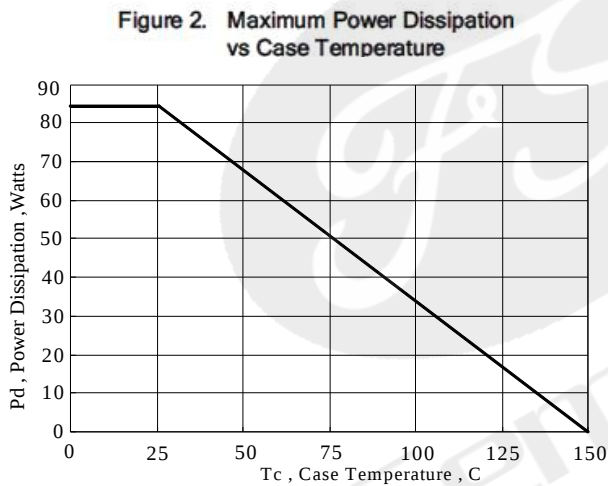
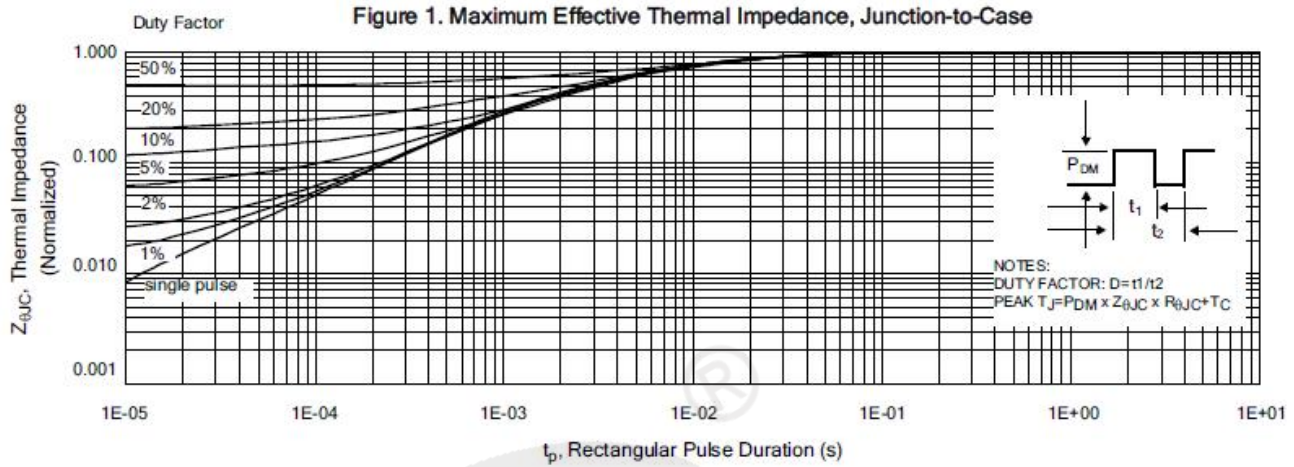


Figure 6. Maximum Peak Current Capability

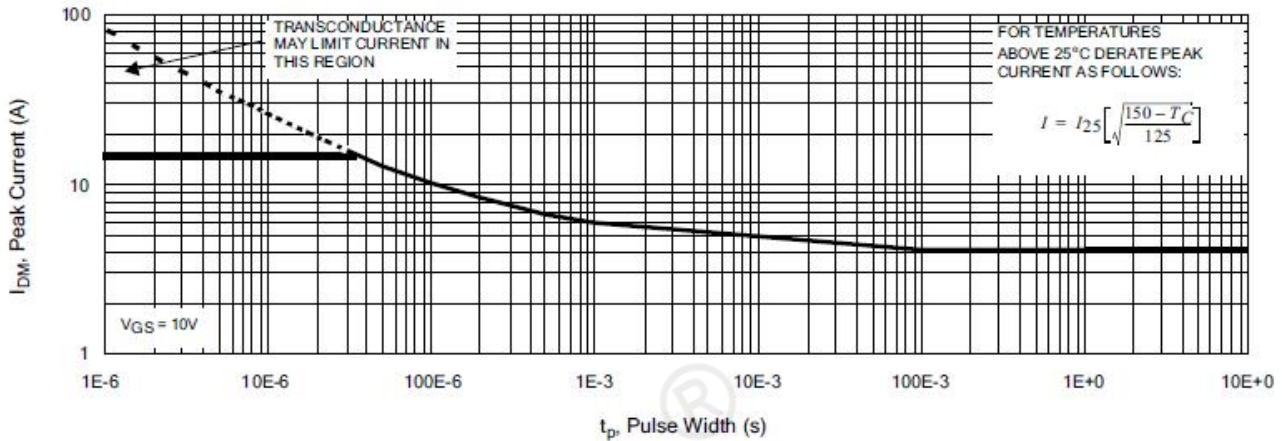


Figure 7. Typical Transfer Characteristics

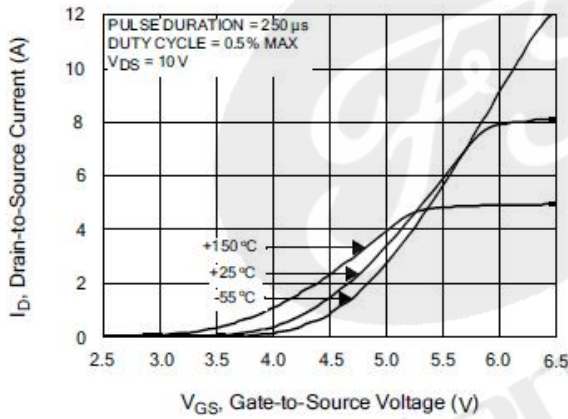


Figure 8. Unclamped Inductive Switching Capability

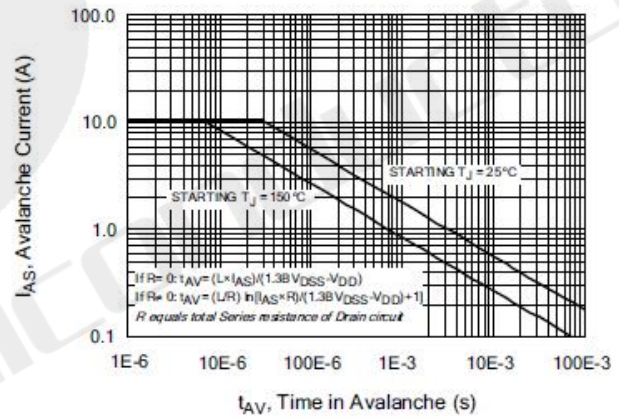


Figure 9. Typical Drain-to-Source ON Resistance vs Drain Current

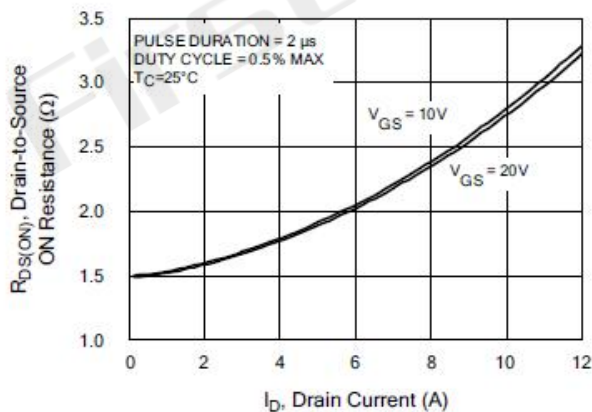


Figure 10. Typical Drain-to-Source ON Resistance vs Junction Temperature

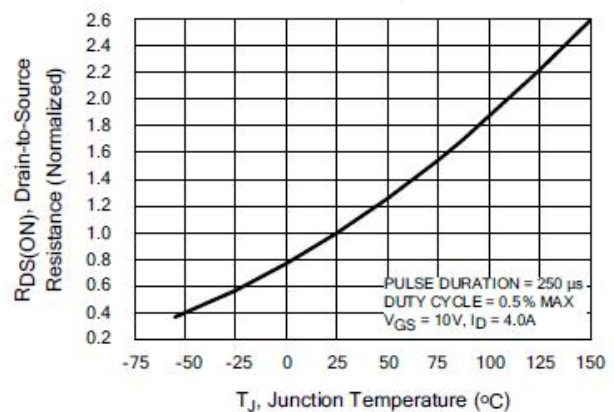


Figure 11. Typical Breakdown Voltage vs Junction Temperature

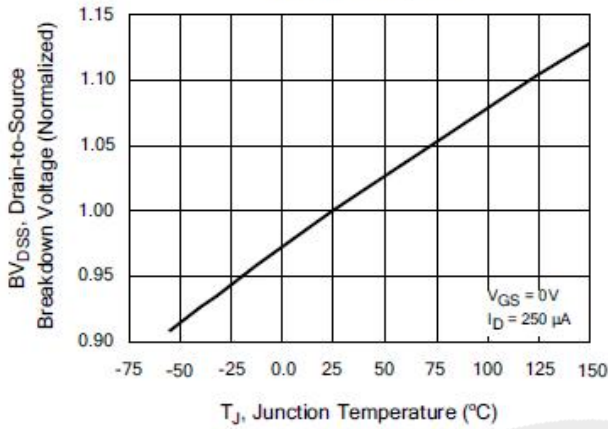


Figure 12. Typical Threshold Voltage vs Junction Temperature

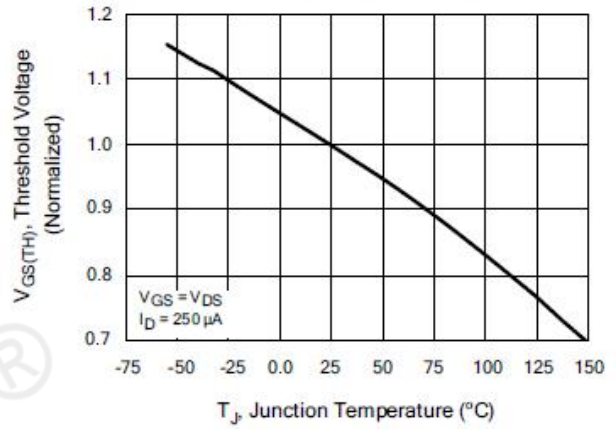


Figure 13. Maximum Forward Bias Safe Operating Area

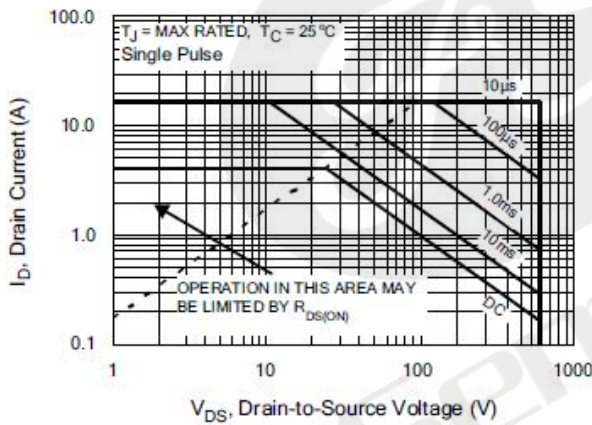


Figure 14. Typical Capacitance vs

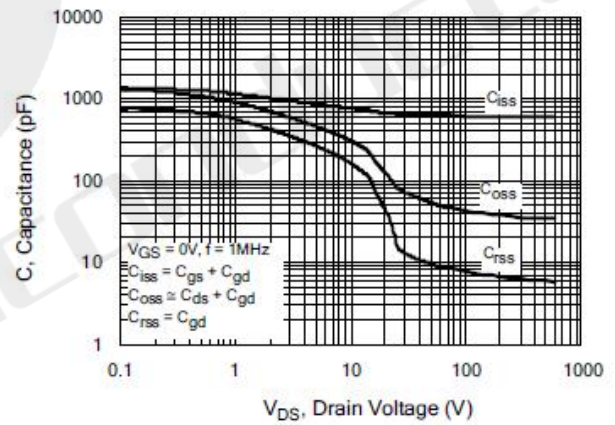


Figure 15. Typical Gate Charge vs Gate-to-Source Voltage

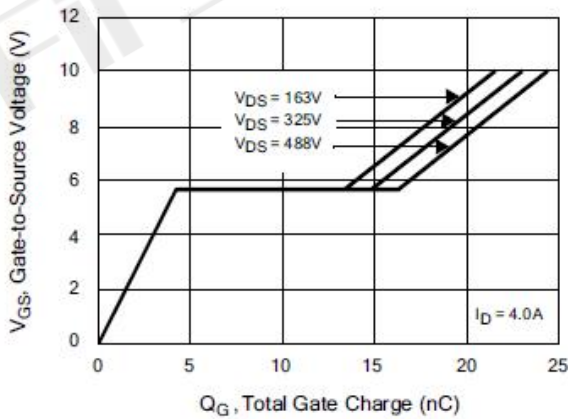
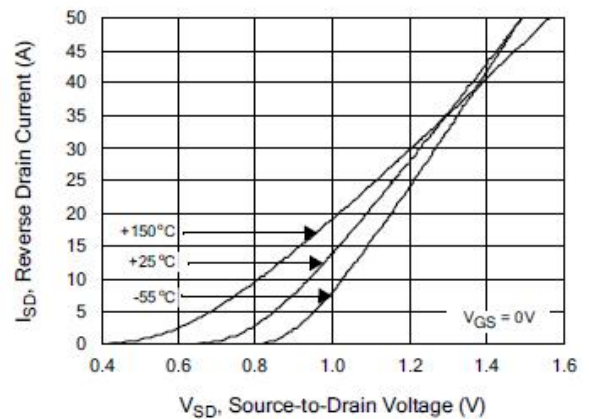


Figure 16. Typical Body Diode Transfer Characteristics



Test Circuit and Waveform

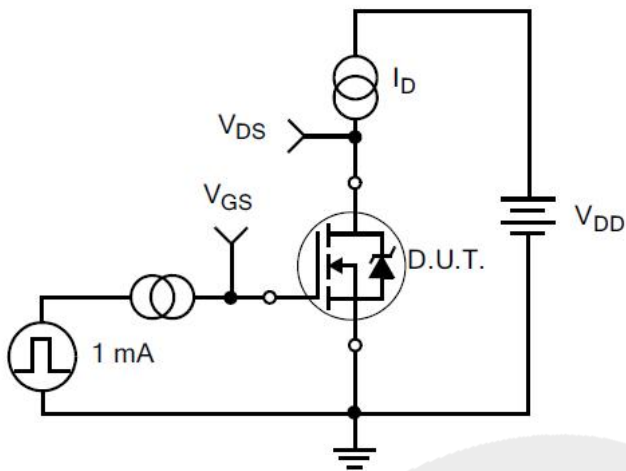


Figure 17. Gate Charge Test Circuit

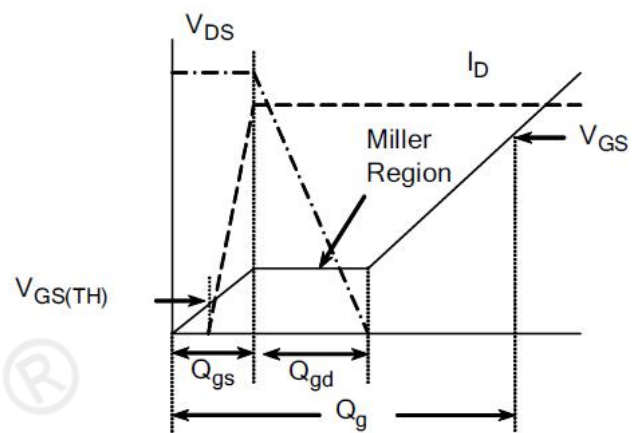


Figure 18. Gate Charge Waveform

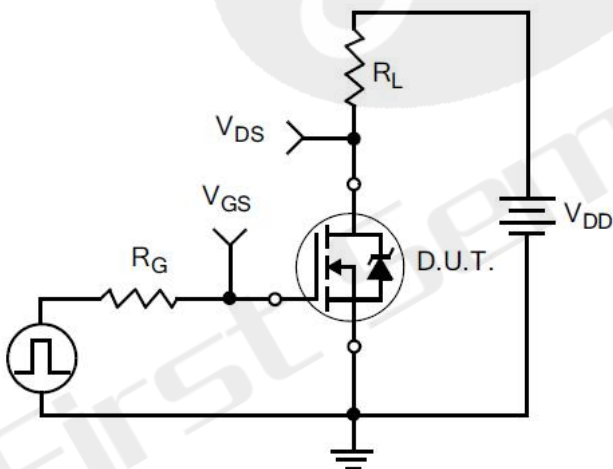


Figure 19. Resistive Switching Test Circuit

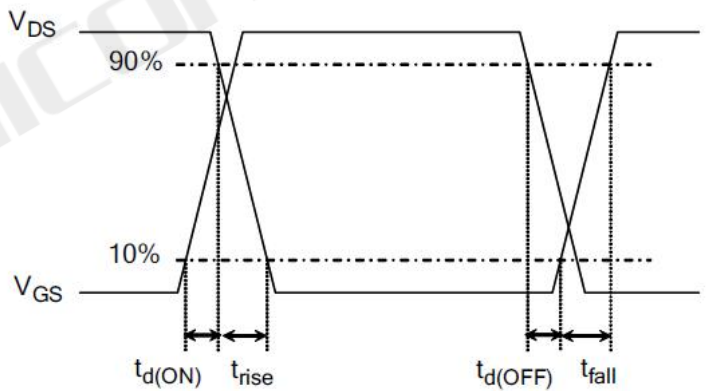


Figure 20. Resistive Switching Waveforms

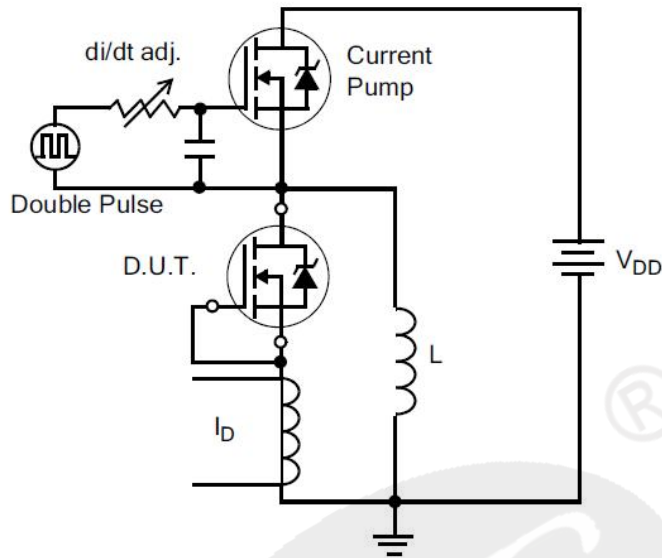


Figure 21. Diode Reverse Recovery Test Circuit

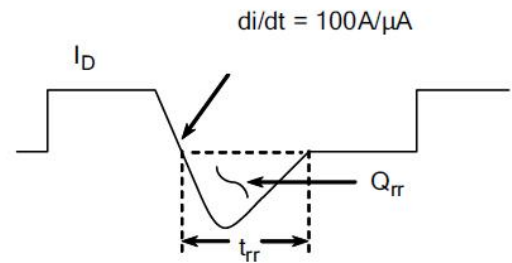


Figure 22. Diode Reverse Recovery Waveform

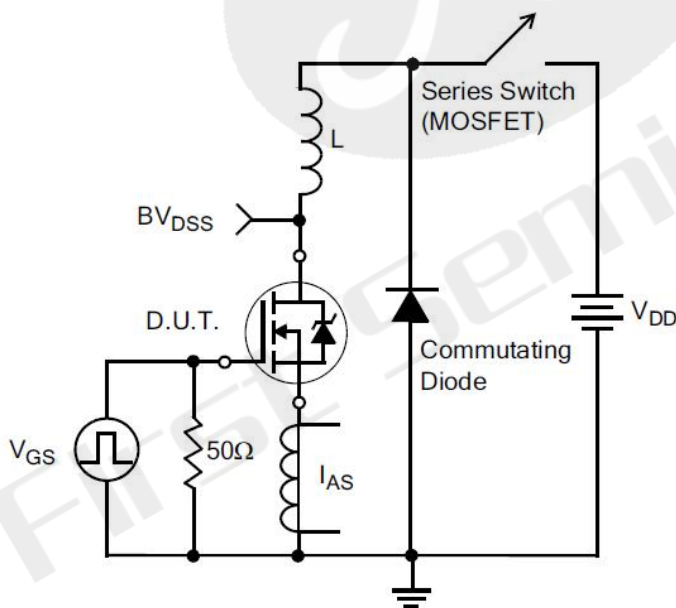


Figure 23. Unclamped Inductive Switching Test Circuit

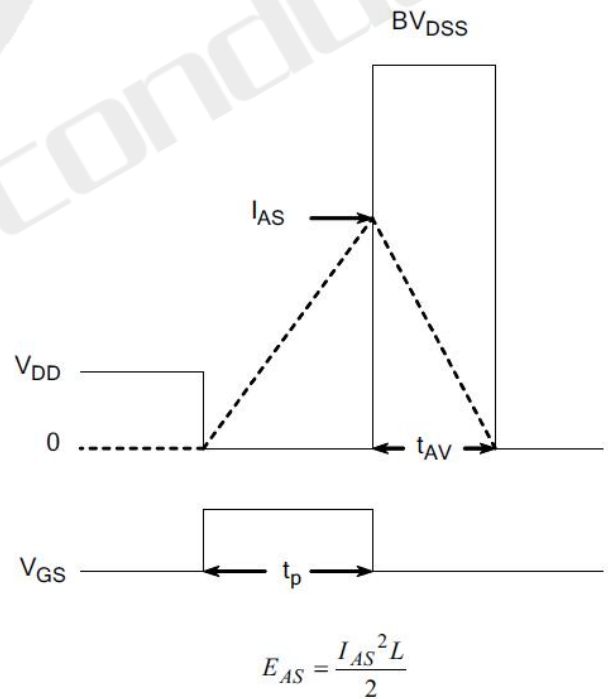
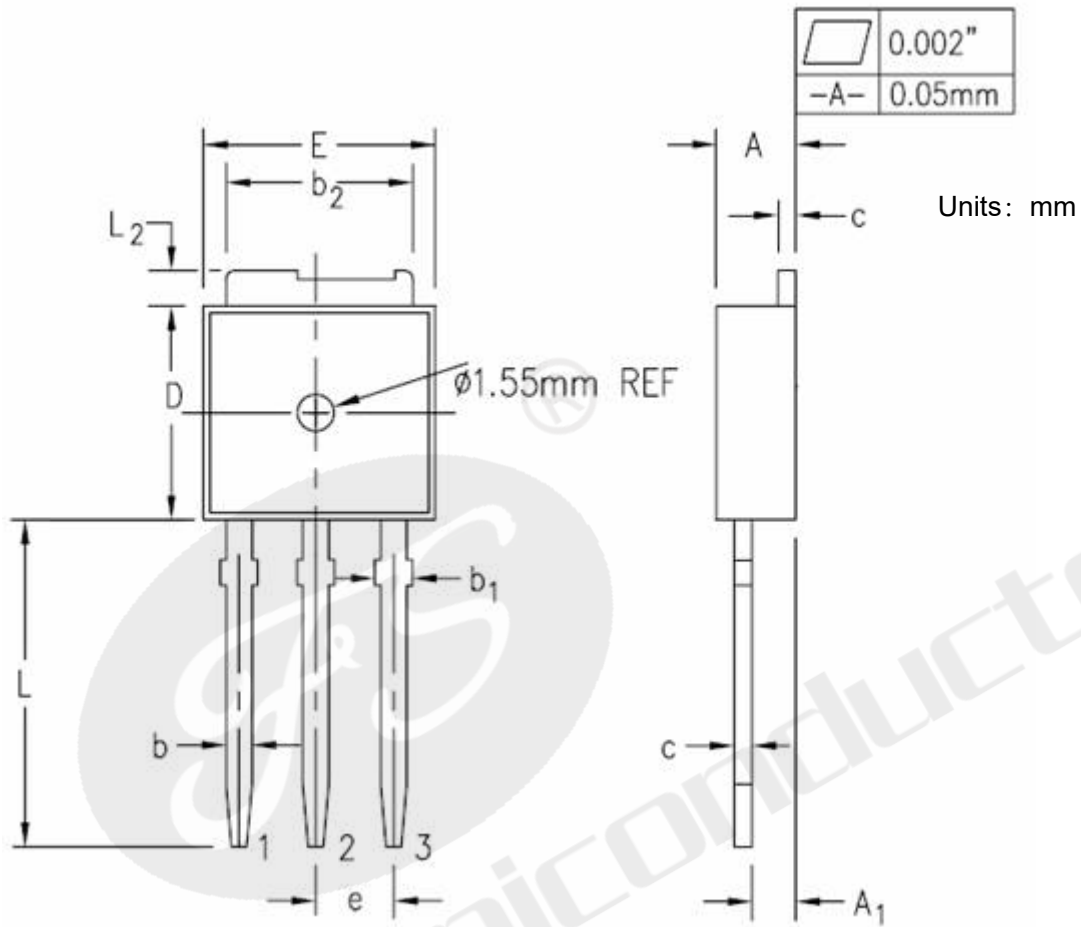


Figure 24. Unclamped Inductive Switching Waveforms

Package Information

TO-251



SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.086	0.094	2.19	2.38	
A1	0.041	0.048	1.04	1.23	
b	0.025	0.035	0.64	0.89	
b1	0.027	0.039	0.69	0.92	
b2	0.206	0.216	5.23	5.48	
c	0.018	0.024	0.46	0.61	
D	0.241	0.249	6.12	6.32	
E	0.250	0.265	6.35	6.73	
e	0.090 TYP.		2.28 TYP.		
L	0.350	0.380	8.89	9.65	
L2	0.035	0.050	0.89	1.27	



Declaration

- FIRST reserves the right to change the specifications, the same specifications of products due to different packaging line mold, the size of the appearance will be slightly different, shipped in kind, without notice! Customers should obtain the latest version information before ordering, and verify whether the relevant information is complete and up-to-date.
- Any semiconductor product under certain conditions has the possibility of failure or failure, The buyer has the responsibility to comply with safety standards and take safety measures when using FIRST products for system design and manufacturing, To avoid To avoid potential failure risks, which may cause personal injury or property damage!
- Product promotion endless, our company will wholeheartedly provide customers with better products!

ATTACHMENT

Revision History

Date	REV	Description	Page
2018.01.01	1.0	Initial release	